

PSMN1R1-25YLC

N-channel 25 V 1.15 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	N	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	-	25	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1] -	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	-	215	W
T _j	junction temperature		-	-55	-	175	°C
Static char	racteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 25 °C; see <u>Figure 12</u>	-	-	1.2	1.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12	-	-	0.95	1.15	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic o	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	39	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	[Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R1-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN1R1-25YLC	1C125L

^{[1] % =} placeholder for manufacturing site code.

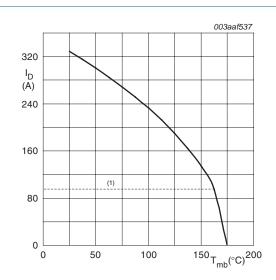
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

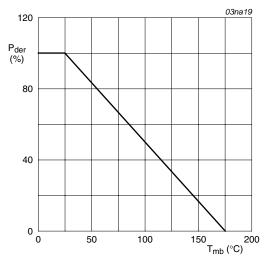
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> [1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u> [1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	1318	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	215	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	810	-	V
Source-drain	n diode				
Is	source current	T _{mb} = 25 °C	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \degree C$	-	1318	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 25 V; unclamped; R_{GS} = 50 Ω; see Figure 3	-	253	mJ

^[1] Continuous current is limited by package.



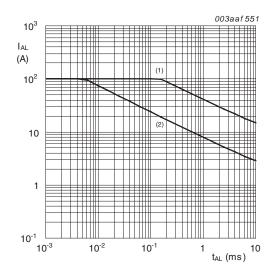
 $V_{GS} \ge 10V$; (1) Capped at 100A due to package

ig 1. Continuous drain current as a function of mounting base temperature



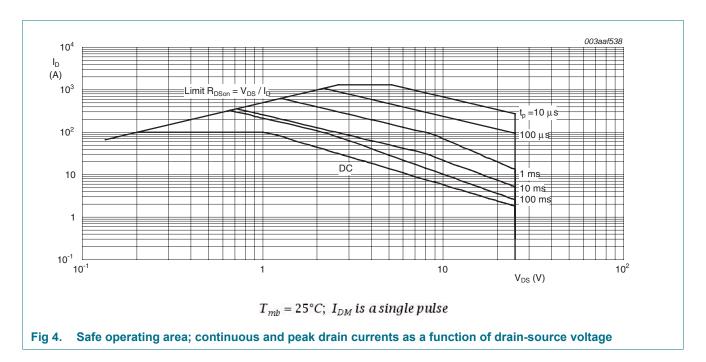
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

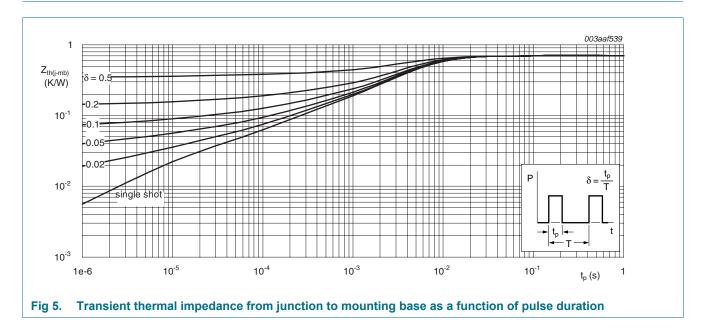
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	0.58	0.7	K/W



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.43	1.95	V
		I_D = 10 mA; V_{DS} = V_{GS} ; T_j = 150 °C	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
		V _{DS} = 25 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μΑ
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nΑ
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nΑ
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u>	-	1.2	1.5	mΩ
	V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	2.45	mΩ	
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u>	-	0.95	1.15	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	1.8	mΩ
R_G	gate resistance	f = 1 MHz	-	1.1	2.2	Ω
Dynamic o	characteristics					
$Q_{G(tot)}$ total gate charge	total gate charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	83	-	nC
		I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	39	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	75	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V;	-	11	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.9	-	nC
Q_{GD}	gate-drain charge		-	11	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.3	-	V
C _{iss}	input capacitance	V _{DS} = 12 V; V _{GS} = 0 V; f = 1 MHz;	-	5287	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1121	-	pF
C _{rss}	reverse transfer capacitance		-	406	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω ; V_{GS} = 4.5 V;	-	35	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	48	-	ns
t _{d(off)}	turn-off delay time		-	74	-	ns
t _f	fall time		-	36	-	ns

 Table 7.
 Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 12 V; f = 1 MHz; T_j = 25 °C	-	22.6	-	nC
Source-drai	n diode					
V _{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see <u>Figure 17</u>	-	8.0	1.1	V
t _{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V;	-	43	-	ns
Q _r	recovered charge	V _{DS} = 12 V	-	42	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 12 \text{ V; see } \frac{\text{Figure } 18}{\text{Figure } 18}$	-	25	-	ns
t _b	reverse recovery fall time		-	18	-	ns

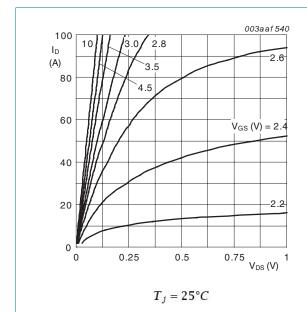
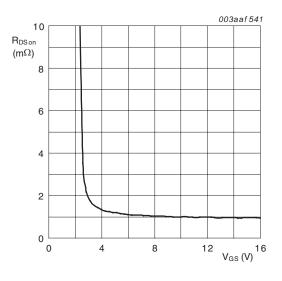
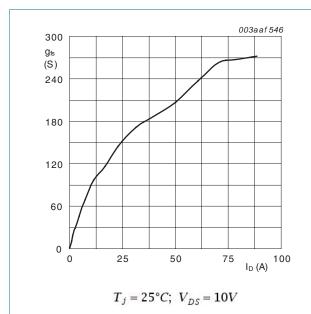


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



Forward transconductance as a function of Fig 8. drain current; typical values

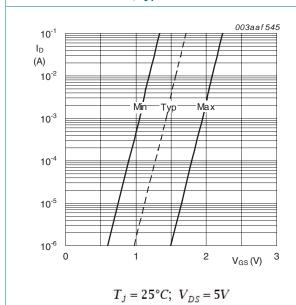
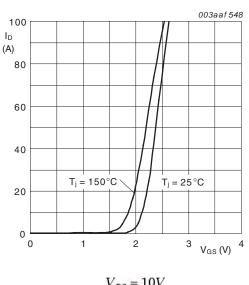
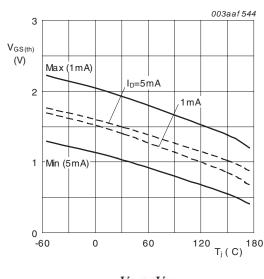


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



 $V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature

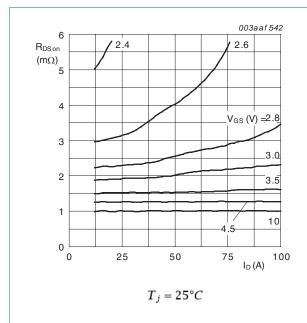


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

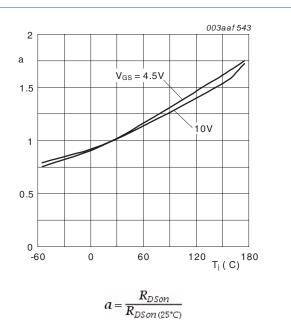


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

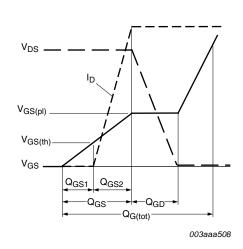
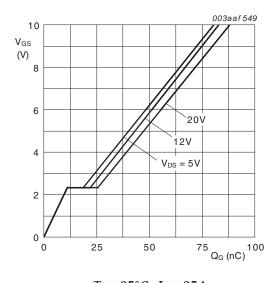


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

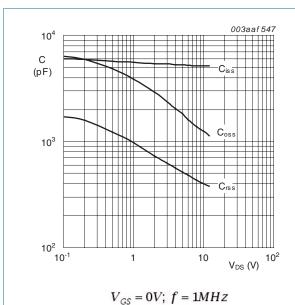


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

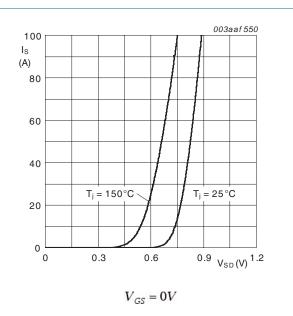


Fig 17. Source current as a function of source-drain voltage; typical values

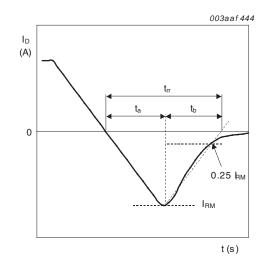


Fig 18. Reverse recovery timing definition

8. Package outline

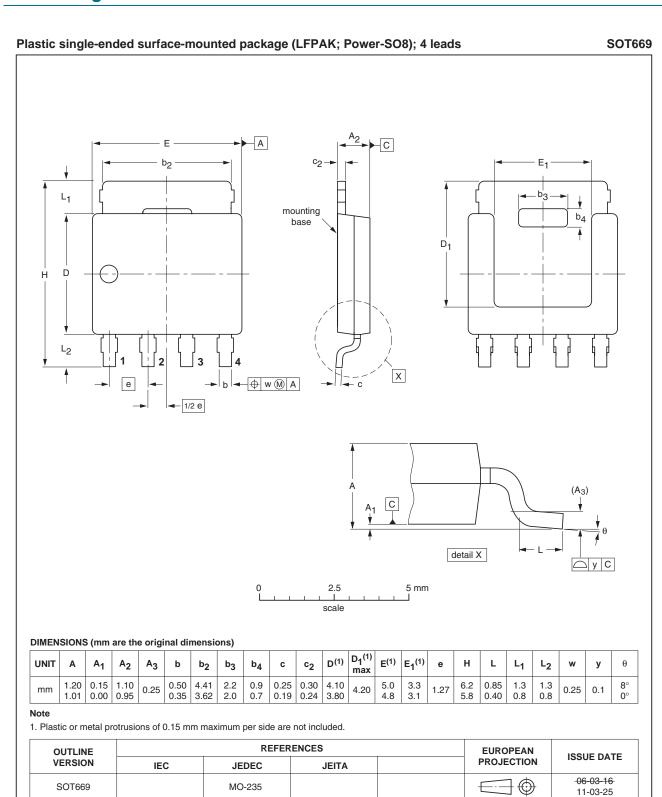


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R1-25YLC

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R1-25YLC v.1	20110502	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel 25 V 1.15 m Ω logic level MOSFET in LFPAK using

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12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking2
5	Limiting values3
6	Thermal characteristics5
7	Characteristics6
8	Package outline
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions
10.3	Disclaimers
10.4	Trademarks14
11	Contact information14